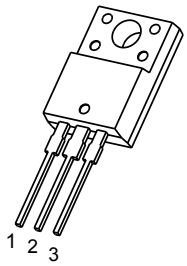
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220F Plastic-Encapsulate MOSFETS

CJPF12N65 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
650V	0.85Ω@10V	12A

TO-220F



1. GATE
2. DRAIN
3. SOURCE

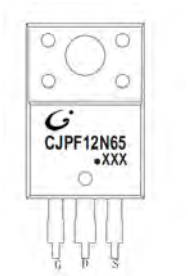
GENERAL DESCRIPTION

This advanced high voltage MOSFET is designed to stand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode fast recovery time. Designed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

FEATURE

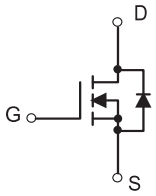
- High Current Rating
- Lower $R_{DS(on)}$
- Low Reverse Transfer Capacitance
- Fast Switching Capability
- Tighter V_{SD} Specifications
- Avalanche Energy Specified

MARKING



CJPF12N65= Device code
Solid dot = Green molding compound device, if none, the normal device
XXX=Date Code

Equivalent Circuit



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GSS}	±30	
Continuous Drain Current	I_D	12	A
Pulsed Drain Current(note1)	I_{DM}	48	
Single Pulsed Avalanche Energy (note2)	E_{AS}	540	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	℃/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~+150	℃
Maximum lead temperure for soldering purposes , 1/8"from case for 5 seconds	T_L	260	

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

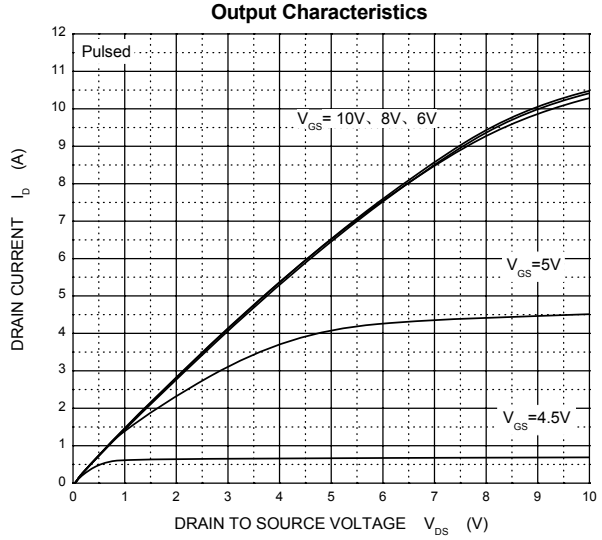
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	650			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =650V, V_{GS} =0V			1	μA
Gate-body leakage curren (note3)	I_{GSS}	V_{DS} =0V, V_{GS} =±30V			±100	nA
On characteristics (note3)						
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	2.0	3.5	4.0	V
Static drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =6A		0.7	0.85	Ω
Dynamic characteristics (note 4)						
Input capacitance	C_{iss}	V_{DS} =25V,V_{GS} =0V,f =1MHz		1800		pF
Output capacitance	C_{oss}			200		
Reverse transfer capacitance	C_{rss}			25		
Switching characteristics (note1,3 4)						
Total gate charge	Q_g	V_{DS} =520V,V_{GS} =10V,I_D =12A		42	54	nC
Gate-source charge	Q_{gs}			8.6		
Gate-drain charge	Q_{gd}			21		
Turn-on delay time	$t_{d(on)}$	V_{DD}=325V, V_{GS}=10V, R_G=25Ω, I_D =12A		30		ns
Turn-on rise time	t_r			90		
Turn-off delay time	$t_{d(off)}$			160		
Turn-off fall time	t_f			90		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note3)	V_{SD}	V_{GS} = 0V, I_S =12A			1.4	V
Maximum continuous drain-source diode forward current	I_S				12	A
Maximum pulsed drain-source diode forward current	I_{SM}				48	A

Notes :

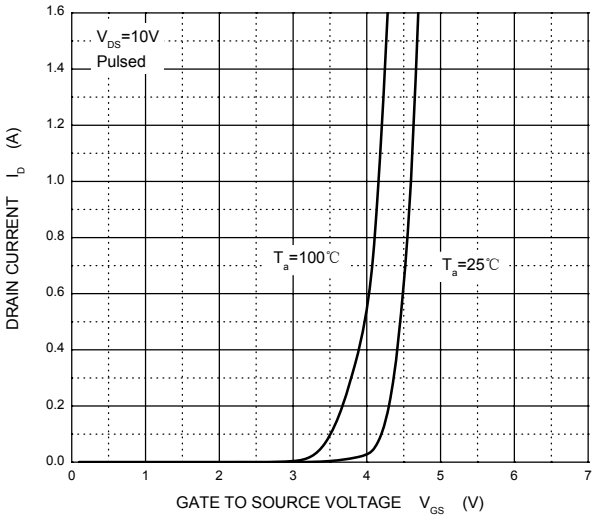
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 7.5mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.
4. These parameters have no way to verify.

Typical Characteristics

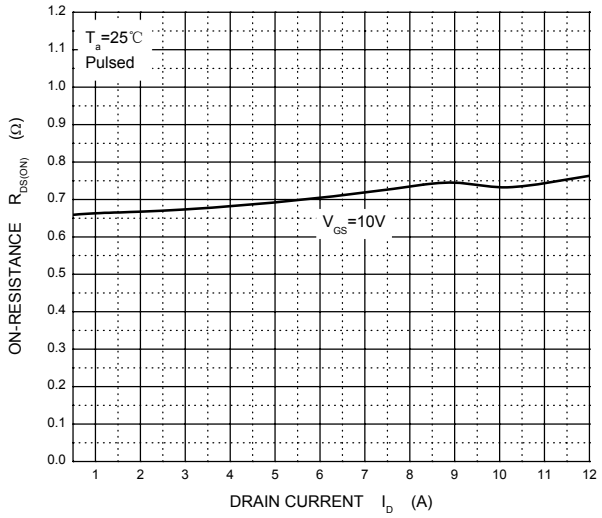
Output Characteristics



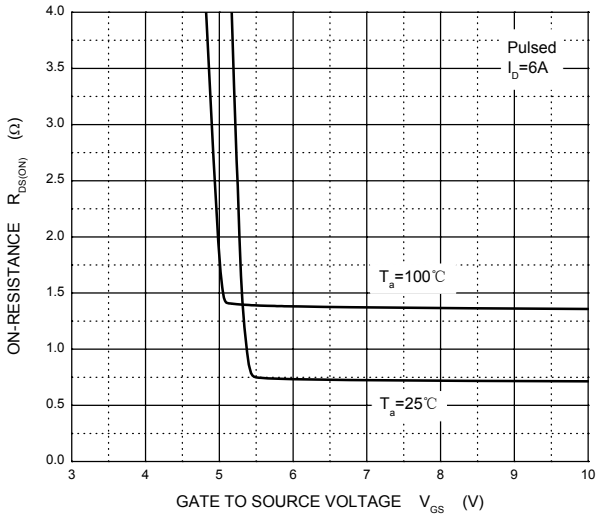
Transfer Characteristics



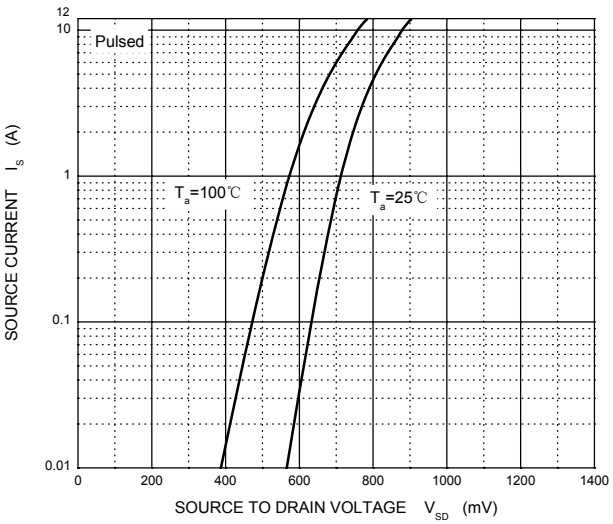
$R_{DS(ON)}$ —— I_D



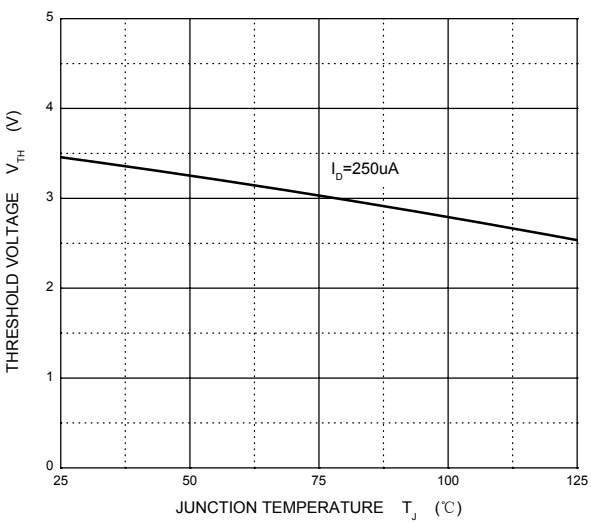
$R_{DS(ON)}$—— V_{GS}



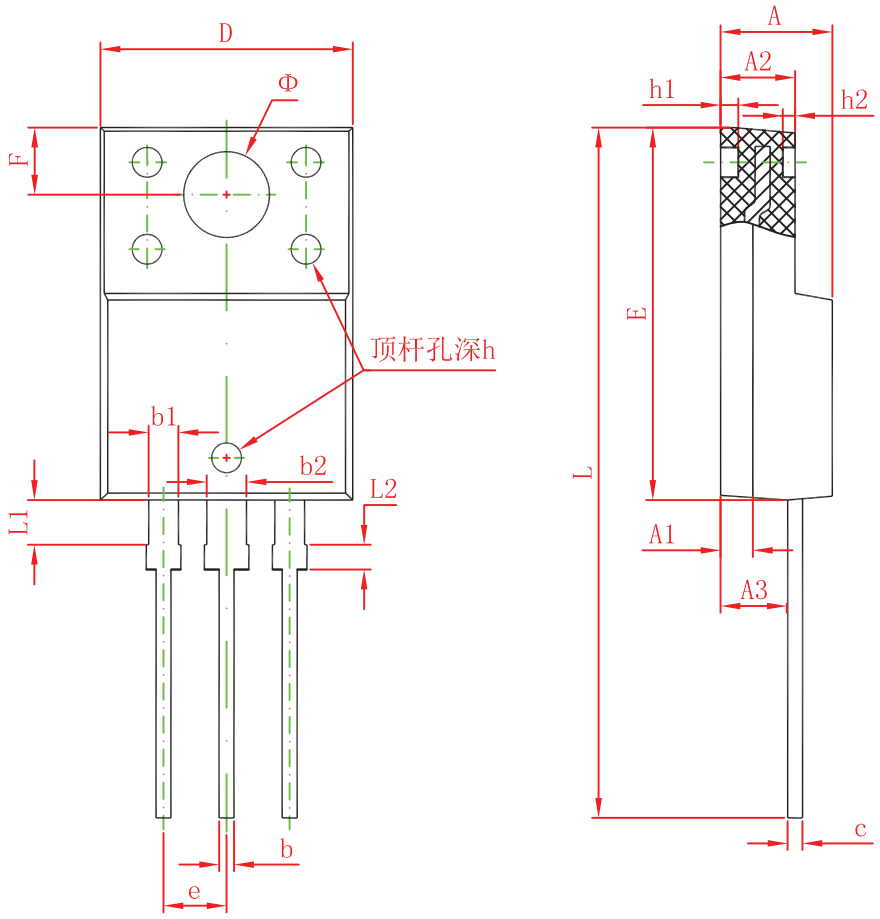
I_S —— V_{SD}



Threshold Voltage



TO-220F Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	0.900	1.100	0.035	0.043